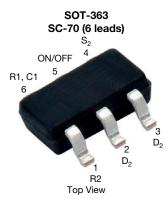
Si1865DDL **Vishay Siliconix**

www.vishay.com

Load Switch with Level-Shift

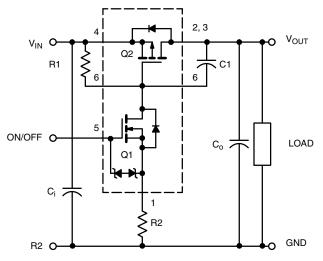


Marking Code: VD

PRODUCT SUMMARY						
V _{DS} (V)	12					
$R_{DS(on)}$ (Ω) at V_{IN} = 4.5 V	0.200					
$R_{DS(on)}$ (Ω) at V_{IN} = 2.5 V	0.300					
$R_{DS(on)}$ (Ω) at V_{IN} = 1.8 V	0.508					
I _D (A)	± 1.1					
Configuration	Level-shift					

APPLICATION CIRCUITS





COMPONENTS						
R1	R1 Pull-up resistor Typical 10 k Ω to 1					
R2	Optional slew-rate control	Typical 0 to 100 k Ω^{a}				
C1	Optional slew-rate control	Typical 1000 pF				

Note

a. Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on

FEATURES

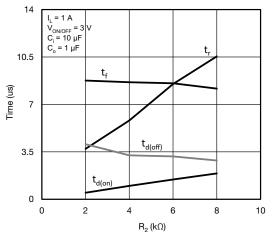
- Low R_{DS(on)} TrenchFET[®]
- 1.8 V to 12 V input
- 1.5 V to 8 V logic level control
- Low profile, small footprint SC-70-6 package
- 2000 V ESD protection on input switch, V_{ON/OFF}
- · Adjustable slew-rate
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Load switch with level-shift
- Slew-rate control
- Portable / consumer devices

DESCRIPTION

The Si1865DDL includes a p- and n-channel MOSFET in a single SC-70-6 package. The low on-resistance p-channel TrenchFET is tailored for use as a load switch. The n-channel, with an external resistor, can be used as a level-shift to drive the p-channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si1865DDL operates on supply lines from 1.8 V to 12 V, and can drive loads up to 1.1 A.



Switching Variation R2 at V_{IN} = 2.5 V, R1 = 20 k Ω

The Si1865DDL is ideally suited for high-side load switching in portable applications. The integrated n-channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.



RoHS COMPLIANT HALOGEN FREE

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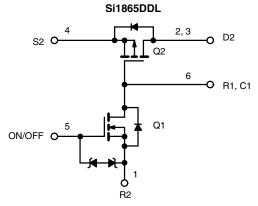
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Si1865DDL

Vishay Siliconix

FUNCTIONAL BLOCK DIAGRAM



ORDERING INFORMATION	
Package	SC-70
Lead (Pb)-free and halogen-free	Si1865DDL-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Input voltage	V _{IN} (V _{DS2})	12	V			
On/off voltage	V _{ON/OFF}	8	v			
Load current	Continuous ^{a, b}	L.	± 1.1			
Load current	Pulsed ^{b, c}	IL I	± 5	А		
Continuous intrinsic diode conduction ^a	I _S	-0.3				
Maximum power dissipation ^a	PD	0.357	W			
Operating junction and storage temperature range	T _J , T _{stg}	-55 to 150	°C			
ESD rating, MIL-STD-883D human body model (100	ESD	2	kV			

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT		
Maximum junction-to-ambient (continuous current) a	R _{thJA}	290	350	°C/W		
Maximum junction-to-foot (Q2)	R _{thJF}	250	300	0/11		

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Off Characteristics	Off Characteristics							
Reverse leakage current	I _{FL}	$V_{IN} = 12 \text{ V}, \text{ V}_{ON/OFF} = 0 \text{ V}$	-	-	1	μA		
Diode forward voltage	V _{SD}	I _S = -0.8 A	-	-0.84	-1.2	V		
On Characteristics								
Input voltage range	V _{IN}		1.8	-	12	V		
On-resistance (p-channel)	R _{DS(on)}	$V_{ON/OFF}$ = 1.5 V, V_{IN} = 4.5 V, I_D = 1.1 A	-	0.165	0.200			
		$V_{ON/OFF} = 1.5 \text{ V}, V_{IN} = 2.5 \text{ V}, I_D = 0.9 \text{ A}$	-	0.250	0.300			
		$V_{ON/OFF} = 1.5 \text{ V}, V_{IN} = 1.8 \text{ V}, I_D = 0.2 \text{ A}$	-	0.376	0.508			
On state (a sharene)) dusia suuraat	I _{D(on)}	$V_{\text{IN-OUT}} \leq 0.2$ V, V_{IN} = 5 V, $V_{\text{ON/OFF}}$ = 1.5 V	1	-	-	А		
On-state (p-channel) drain-current		$V_{\text{IN-OUT}} \leq 0.3$ V, V_{IN} = 3 V, $V_{\text{ON/OFF}}$ = 1.5 V	1	-	-			

Notes

a. Surface mounted on FR4 board

b. $V_{IN} = 12$ V, $V_{ON/OFF} = 8$ V, $T_A = 25$ °C

c. Pulse test: pulse width \leq 300 µs, duty cycle \leq 2 %

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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1.8

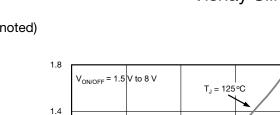
V_{DROP} (V)

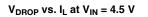
0.9

0.5

0.0

0





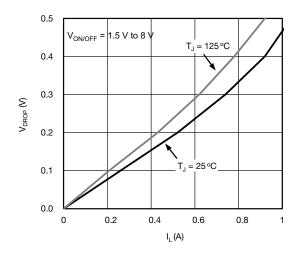
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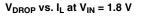
3 I_L (A)

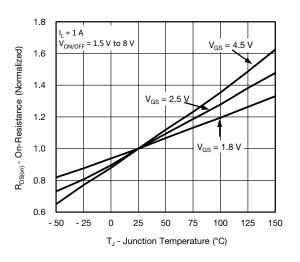
Т 25 °C

4.5

6







Normalized On-Resistance vs. Junction Temperature

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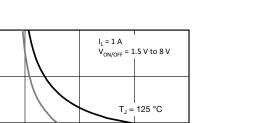
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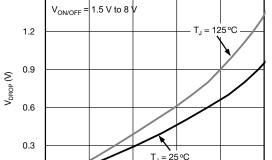
 $V_{\rm IN}$ - (V)

V_{DROP} vs. V_{IN} at I_L = 1 A



T_J = 25 °C

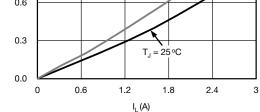
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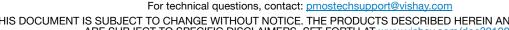
1

V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics



 V_{DROP} vs. I_L at V_{IN} = 2.5 V



8

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5

4

3

2

1

0

1.5

0.4

0.3

0.2

0.1

0 0

V_{DROP} (V)

0

0.5

I_D - Drain Current (A)



5 V thru 3 V

V_{GS} =2.5V

V_{GS} =2V

V_{GS} =1.8V

V_{GS} = 1.5 V

2

1.5

 V_{GS}

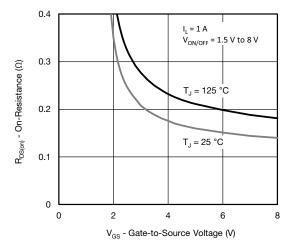
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Si1865DDL

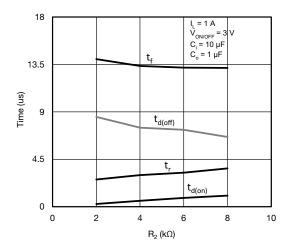


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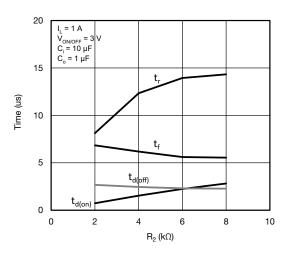
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



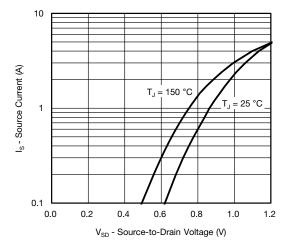
On-Resistance vs. Input Voltage



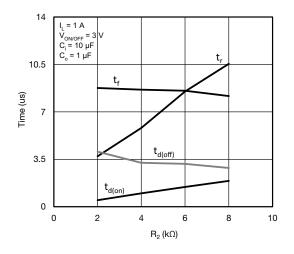
Switching Variation R2 at V $_{\text{IN}}$ = 4.5 V, R1 = 20 k Ω

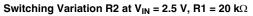


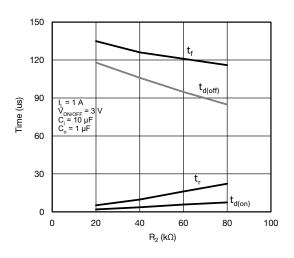
Switching Variation R2 at V $_{\text{IN}}$ = 1.8 V, R1 = 20 k Ω



Source-Drain Diode Forward Voltage







Switching Variation R2 at V_{IN} = 4.5 V, R1 = 300 k Ω

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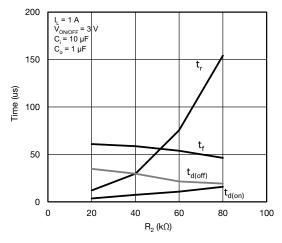
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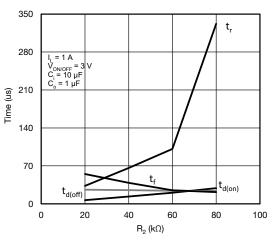


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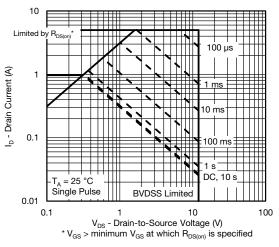
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



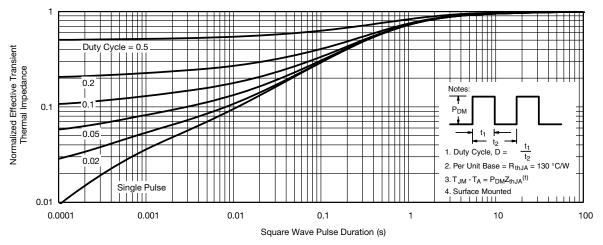
Switching Variation R2 at V_{IN} = 2.5 V, R1 = 300 k Ω



Switching Variation R2 at V_{IN} = 1.8 V, R1 = 300 k Ω



Safe Operating Area, Junction-to-Foot



Normalized Thermal Transient Impedance, Junction-to-Ambient

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Package Information Vishay Siliconix

SC-70: 6-LEADS





	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	-	1.10	0.035	-	0.043
A ₁	-	-	0.10	-	-	0.004
A ₂	0.80	-	1.00	0.031	-	0.039
b	0.15	-	0.30	0.006	0.006 –	
С	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Е	1.80	2.10	2.40	0.071 0.083		0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65BSC			0.026BSC	;
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
٩	7°Nom				7°Nom	
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550						

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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